

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / PROFESSIONAL

PART NUMBER: RHRG75120

MANUFACTURER: INTERSIL

REMARK: TC= 110C

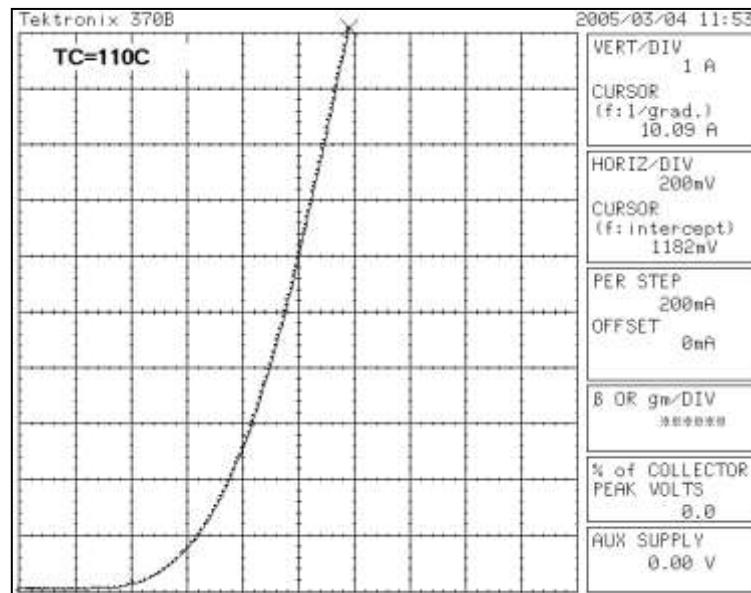


Bee Technologies Inc.

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

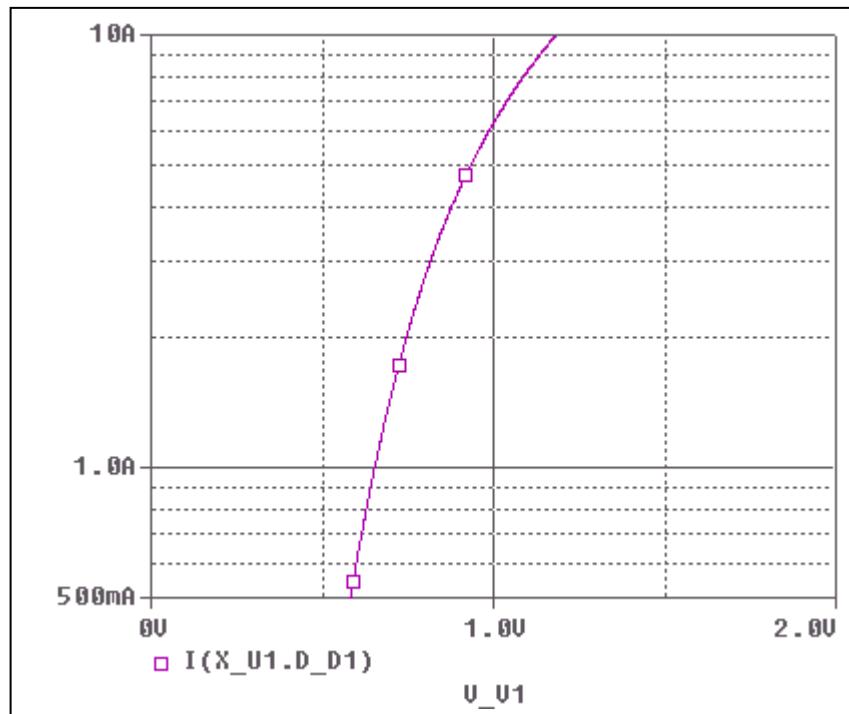
Forward Current Characteristic

Reference

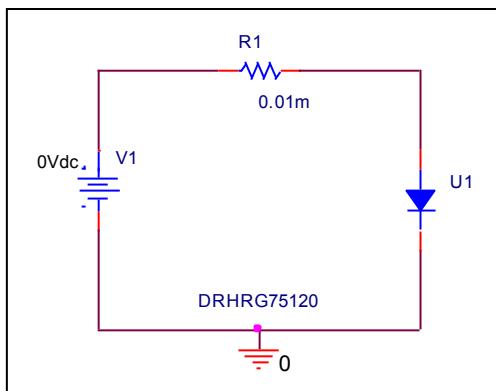


Forward Current Characteristic

Circuit Simulation Result

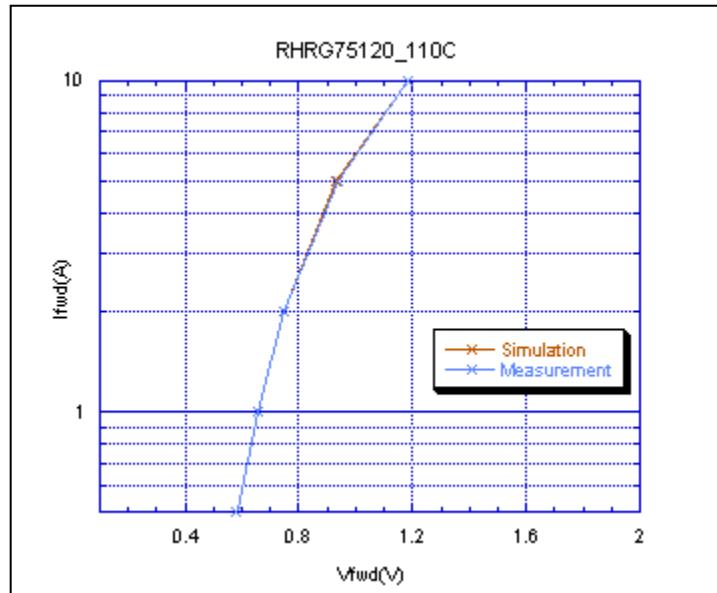


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

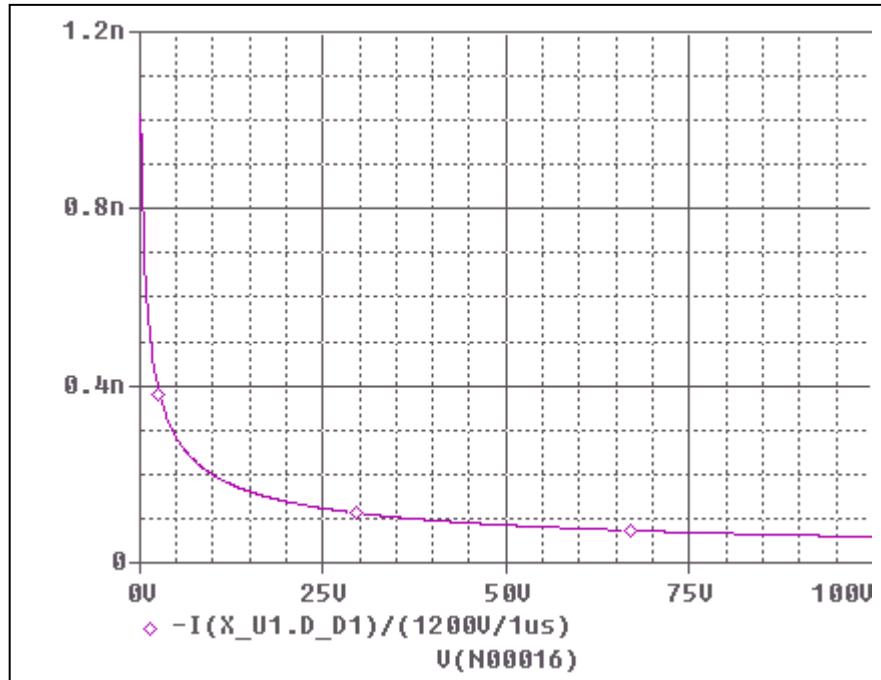


Simulation Result

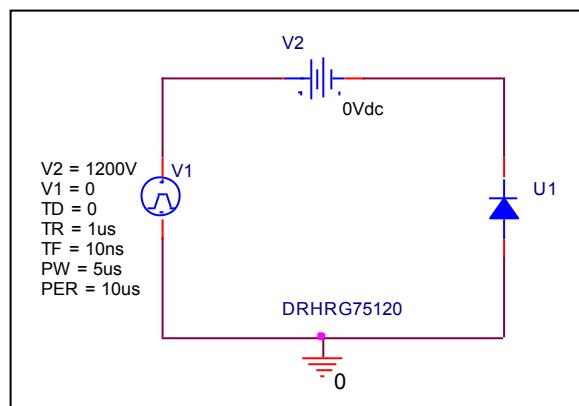
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.5	0.576	0.581	-0.87
1	0.654	0.653	0.15
2	0.750	0.747	0.40
5	0.934	0.933	0.11
10	1.182	1.182	0.00

Capacitance Characteristic

Circuit Simulation Result

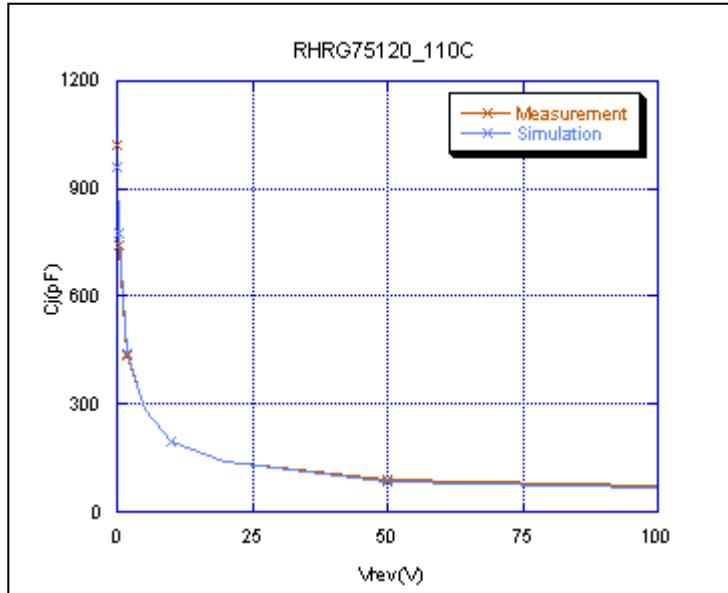


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

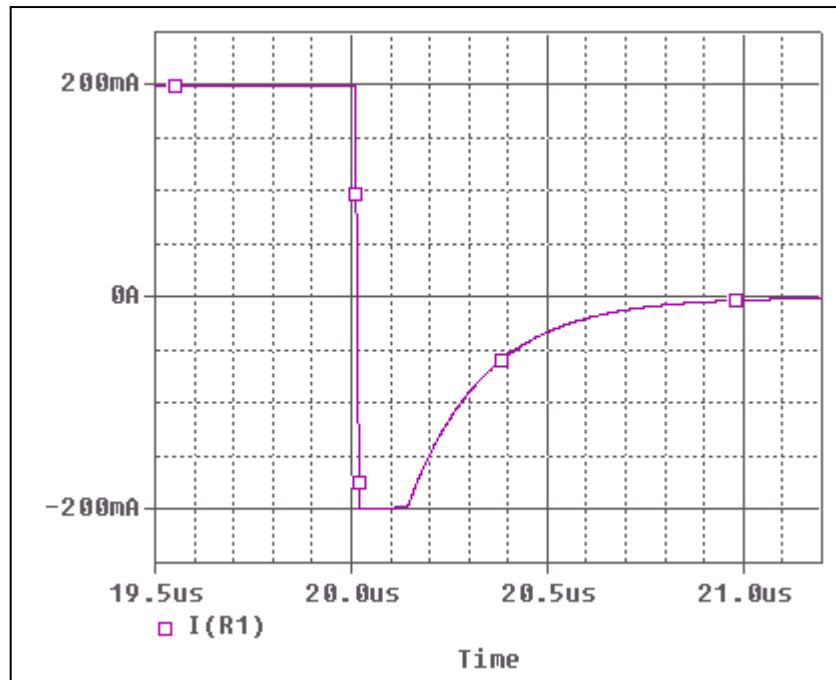


Simulation Result

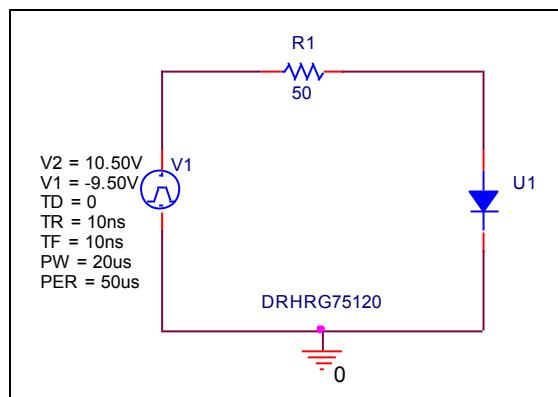
$V_{rev}(V)$	$C_j(pF)$ Measurement	$C_j(pF)$ Simulation	%Error
0	1134.000	1134.000	0.00
0.1	1021.000	959.978	5.98
0.2	930.100	952.261	-2.38
0.5	740.274	777.189	-4.99
1	578.190	596.334	-3.14
2	434.846	442.363	-1.73
5	283.081	285.947	-1.01
10	195.437	198.719	-1.68
20	138.995	138.247	0.54

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

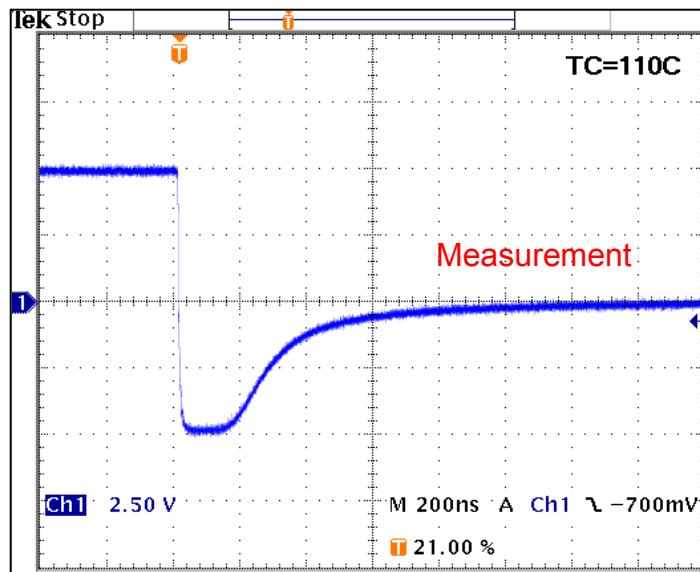


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trj	132	ns	13.2	ns	0.151
trb	452	ns	452.1	ns	0.022

Reverse Recovery Characteristic

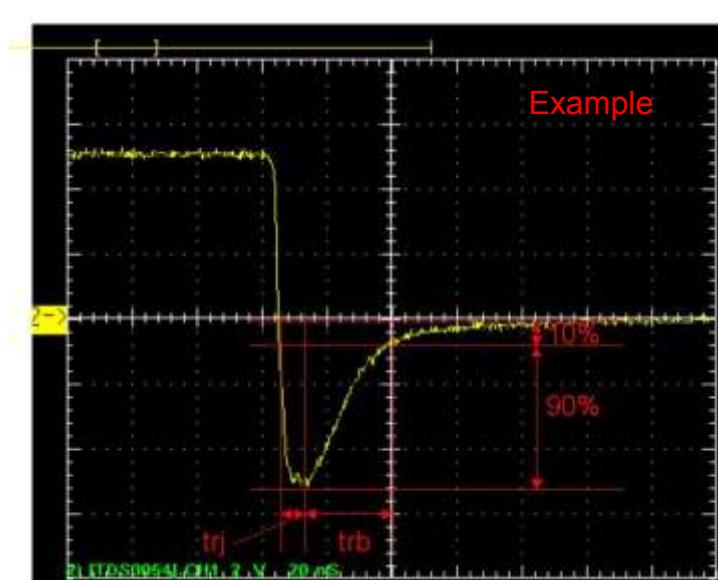
Reference



Trj =132 (ns)

Trb= 452 (ns)

Conditions: Ifwd=Irev=0.2(A), RI=50



Relation between trj and trb